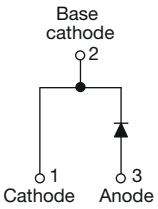
HEXFRED® Ultrafast Soft Recovery Diode, 4 A

TO-220AC 2L



FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA04TB60 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to “snap-off” during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	4 A
V_R	600 V
V_F at I_F	1.4 V
t_{rr} typ.	17 ns
T_J max.	150 °C
Package	TO-220AC 2L
Circuit configuration	Single

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V_R		600	V
Maximum continuous forward current	I_F	T_C = 100 °C	4	A
Single pulse forward current	I_{FSM}		25	
Maximum repetitive forward current	I_{FRM}		16	
Maximum power dissipation	P_D	T_C = 25 °C	25	W
		T_C = 100 °C	10	
Operating junction and storage temperature range	T_J, T_{Stg}		-55 to +150	°C

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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Cathode to anode breakdown voltage	V_{BR}	I_R = 100 µA		600	-	-	V
Maximum forward voltage	V_{FM}	I_F = 4.0 A	See fig. 1	-	1.5	1.8	
		I_F = 8.0 A		-	1.8	2.2	
		I_F = 4.0 A, T_J = 125 °C		-	1.4	1.7	
Maximum reverse leakage current	I_{RM}	V_R = V_R rated	See fig. 2	-	0.17	3.0	µA
		T_J = 125 °C, V_R = 0.8 x V_R rated		-	44	300	
Junction capacitance	C_T	V_R = 200 V	See fig. 3	-	4.0	8.0	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Reverse recovery time See fig. 5, 6 and 16	t_{rr}	I_F = 1.0 A, dI_F/dt = 200 A/µs, V_R = 30 V		-	17	-	ns
	t_{rr1}	T_J = 25 °C	I_F = 4 A dI_F/dt = 200 A/µs V_R = 200 V	-	28	42	
	t_{rr2}	T_J = 125 °C		-	38	57	
Peak recovery current See fig. 7 and 8	I_{RRM1}	T_J = 25 °C		-	2.9	5.2	A
	I_{RRM2}	T_J = 125 °C		-	3.7	6.7	
Reverse recovery charge See fig. 9 and 10	Q_{rr1}	T_J = 25 °C		-	40	60	nC
	Q_{rr2}	T_J = 125 °C		-	70	105	
Peak rate of fall of recovery current during t_b See fig. 11 and 12	$dI_{(rec)M}/dt1$	T_J = 25 °C		-	280	-	A/µs
	$dI_{(rec)M}/dt2$	T_J = 125 °C		-	235	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Lead temperature	T_{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R_{thJC}		-	-	5.0	K/W
Thermal resistance, junction to ambient	R_{thA}	Typical socket mount	-	-	80	
Thermal resistance, case to heatsink	R_{thS}	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style 2L TO-220AC	HFA04TB60			

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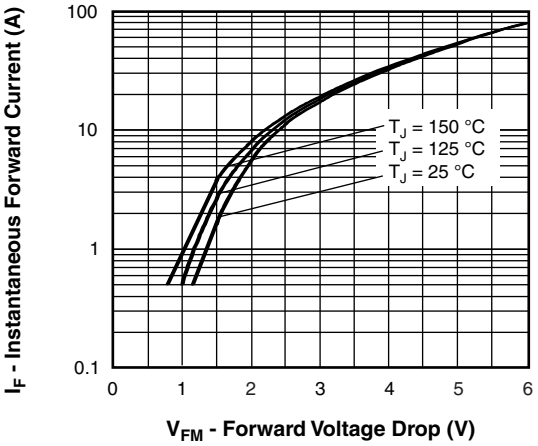

Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

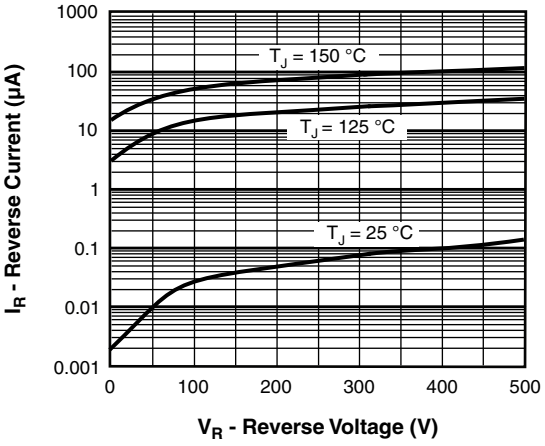

Fig. 2 - Typical Reverse Current vs. Reverse Voltage

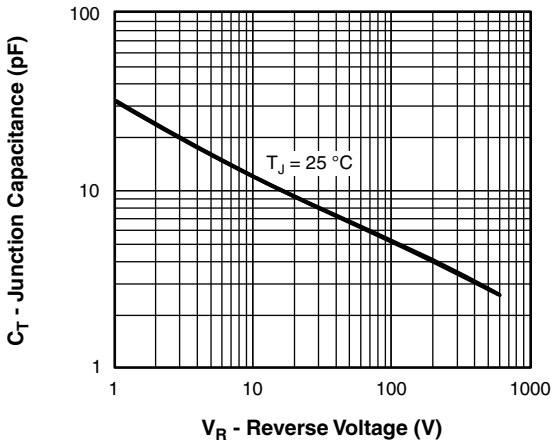

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

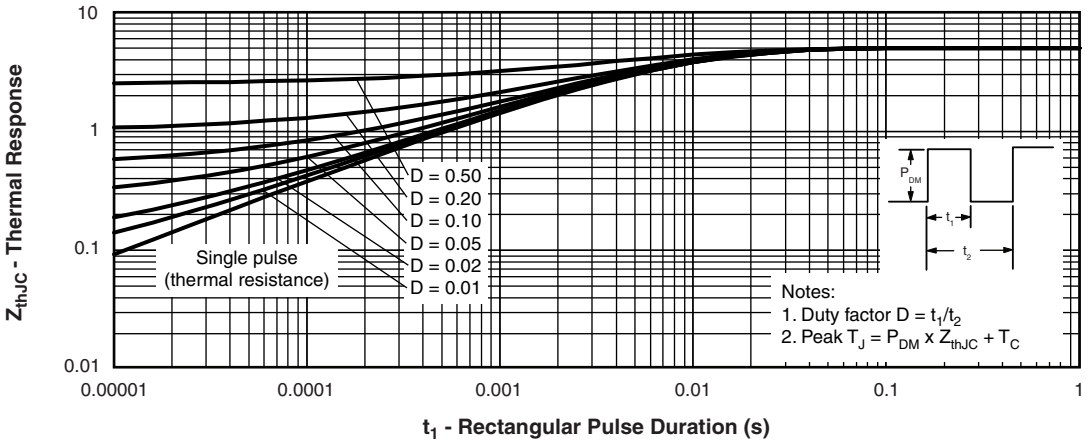

Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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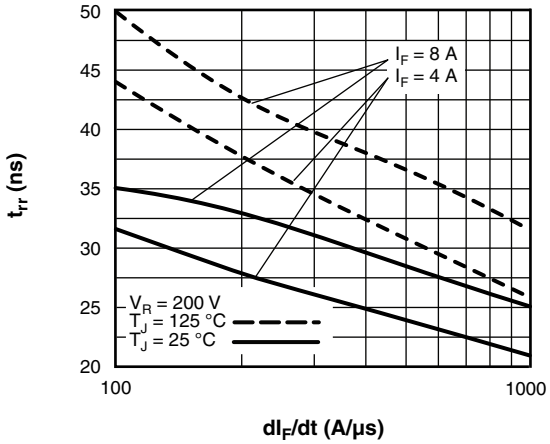


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

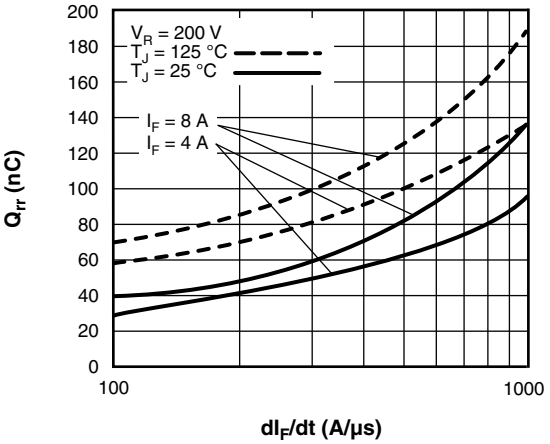


Fig. 7 - Typical Stored Charge vs. dI_F/dt

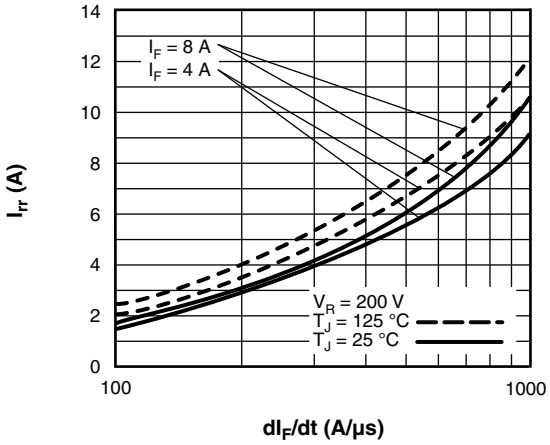


Fig. 6 - Typical Recovery Current vs. dI_F/dt

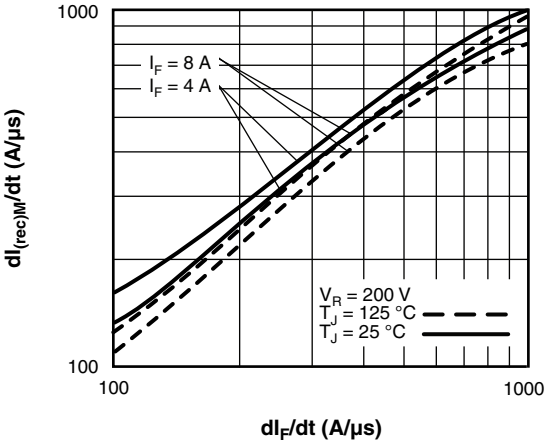
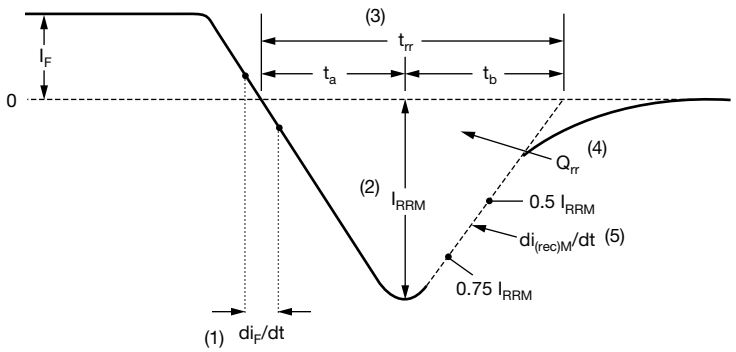


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt



(1) di_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

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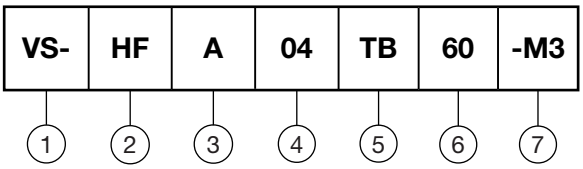
ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product
2 - HEXFRED® family
3 - Electron irradiated
4 - Current rating (04 = 4 A)
5 - Package:
TB = 2L TO-220AC
6 - Voltage rating (60 = 600 V)
7 - Environmental digit:
-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)		
PREFERRED P/N	**BASE QUANTITY**	**PACKAGING DESCRIPTION**
VS-HFA04TB60-M3	50	Antistatic plastic tube

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96156
Part marking information	www.vishay.com/doc?95391

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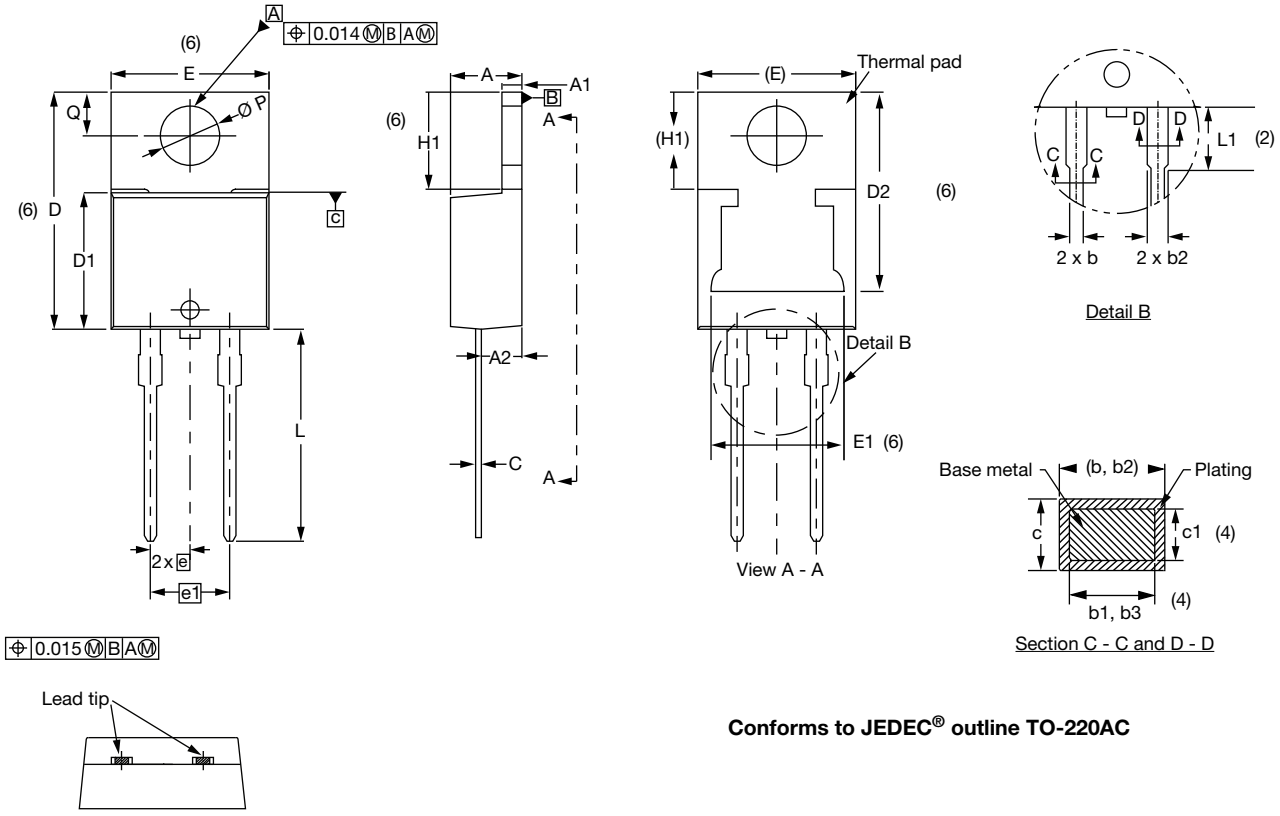
TO-220AC 2L

DIMENSIONS in millimeters and inches



Conforms to JEDEC® outline TO-220AC

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
c	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
e	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
Ø P	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

(1) Dimensioning and tolerancing as per ASME Y14.5M-1994
(2) Lead dimension and finish uncontrolled in L1
(3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
(4) Dimension b1, b3, and c1 apply to base metal only
(5) Controlling dimensions: inches
(6) Thermal pad contour optional within dimensions E, H1, D2, and E1
(7) Outline conforms to JEDEC® TO-220, except D2

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